WS4A004065E0

Silicon Carbide Schottky Diode

G4 MPS Technology

V_{RRM}	=	650	V
I_F (T_C 5)	=	8	A
Q_C	=	11.5	nC

Features

- New Thin Wafer Technology
- Low Forward Voltage Drop (V_F)
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on V_F
- Temperature-independent Switching

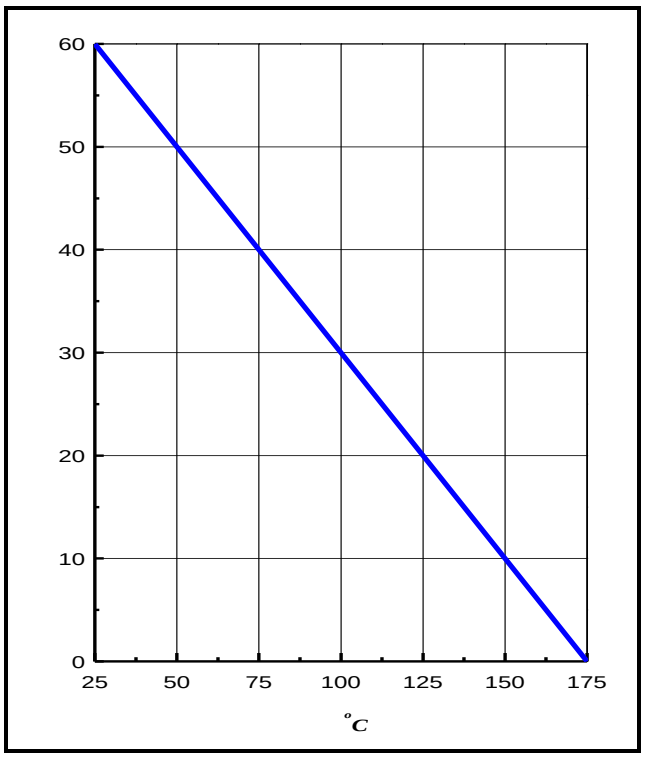
Package

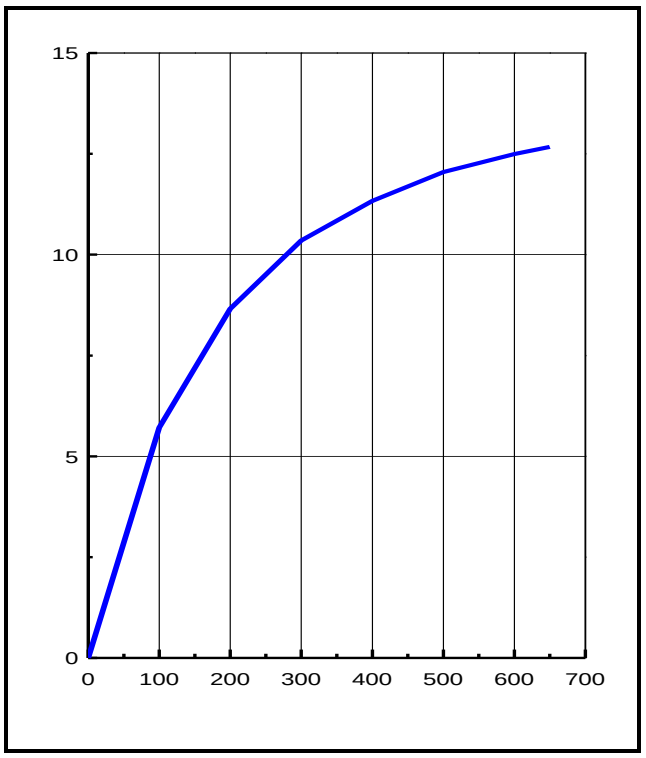


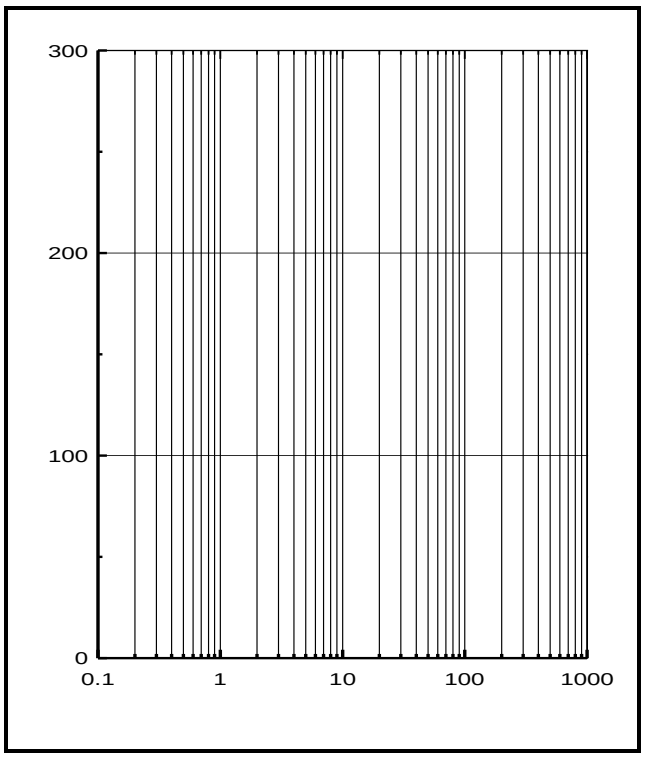
Benefits

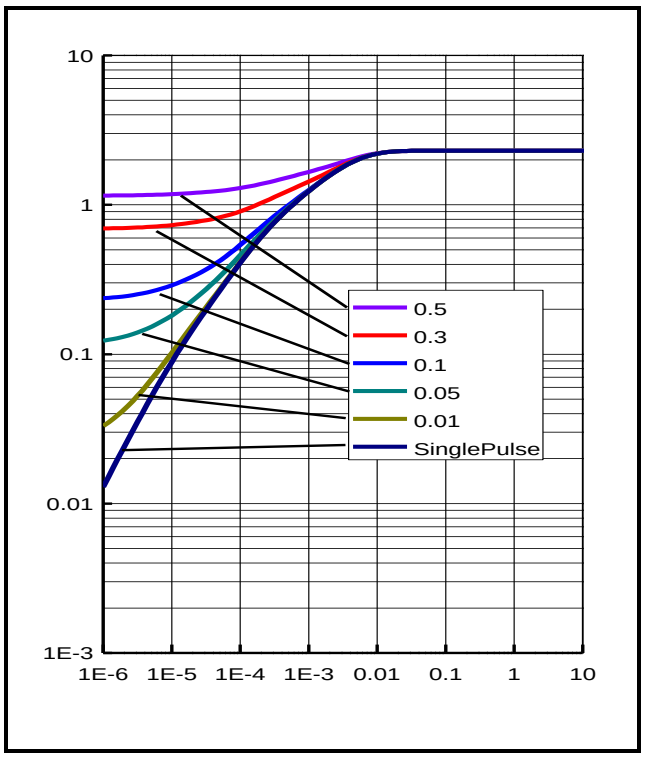
- Replace Bipolar with Unipolar Device
- Reduction of Hea*nBen-UkSUSzUnipolar en-bUS

Typical Performance

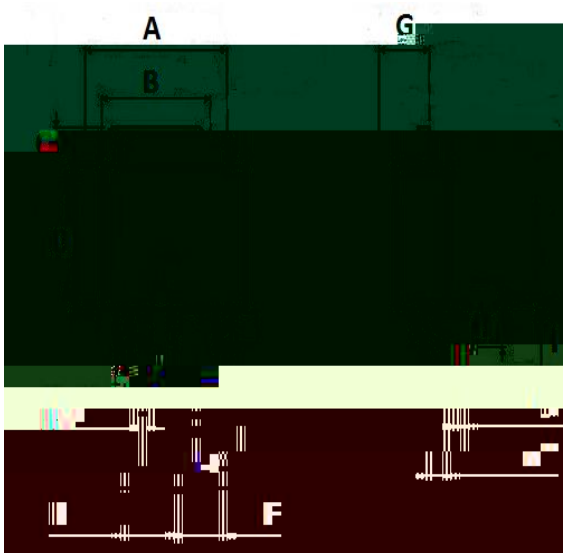








Package Dimensions



1) Before using our products, please contact our marketing managers and get the latest specifications.

2) Ongoing efforts are being made to improve the reliability and quality of the products by CETC, but the semiconductors can malfunction due to various factors. Therefore, in order to prevent artificial damage or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-

the use of our products beyond the rating specified by CETC.

3) All the information contained in this document, such as -6(h)-3( )-188(a)9(s)-6(i6)-3(x)20-6(a)9(g)-34(e)-3(a)9(s)-64

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